

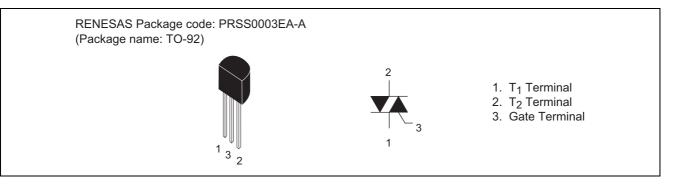
Triac Low Power Use

> REJ03G1248-0200 Rev.2.00 Nov 30, 2007

## Features

- $I_{T(RMS)}$ : 1 A
- $V_{DRM}$  : 600 V
- www.DataSheet  $U.I_{FGTI}^{om}$ ,  $I_{RGTI}$ ,  $I_{RGT III}$ : 7 mA

## Outline



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Non-Insulated Type

Planar Passivation Type

# Applications

Contactless AC switch, fan motor, rice-cooker, electric pot, air cleaner, heater, refrigerator, washing machine, electric fan, vending machine, trigger circuit for low and medium triac, and other general purpose control applications

# **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
Falalletei	Symbol	12		
Repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DRM</sub>	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DSM</sub>	720	V	

### BCR1AM-12A

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	1.0	A	Commercial frequency, sine full wave $360^{\circ}$ conduction, Tc = $56^{\circ}C^{Note3}$
Surge on-state current	I <sub>TSM</sub>	10	A	60Hz sinewave 1 full cycle, peak value non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	0.41	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P <sub>GM</sub>	1	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.1	W	
Peak gate voltage	V <sub>GM</sub>	6	V	
Peak gate current	I <sub>GM</sub>	0.5	A	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
eMassim		0.23	g	Typical value

Notes: 1. Gate open.

# **Electrical Characteristics**

Parameter		Symbol Rated value			е	Unit	Test conditions
		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>		_	0.5	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		V <sub>TM</sub>	_	—	1.6	V	$Tc = 25^{\circ}C$ , $I_{TM} = 1.5 A$ , Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	Ι	V <sub>FGTI</sub>	_	_	2.0	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V <sub>RGTI</sub>	_	_	2.0	V	$R_G = 330 \Omega$
	III	V <sub>RGTIII</sub>		_	2.0	V	
Gate trigger current <sup>Note2</sup>	Ι	I <sub>FGTI</sub>	_	_	7	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	I <sub>RGTI</sub>		_	7	mA	$R_G = 330 \Omega$
	III	I <sub>RGTIII</sub>		_	7	mA	
Gate non-trigger voltage		$V_{GD}$	0.1	_	—	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>		_	50	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	2	—	—	V/µs	Tj = 125°C

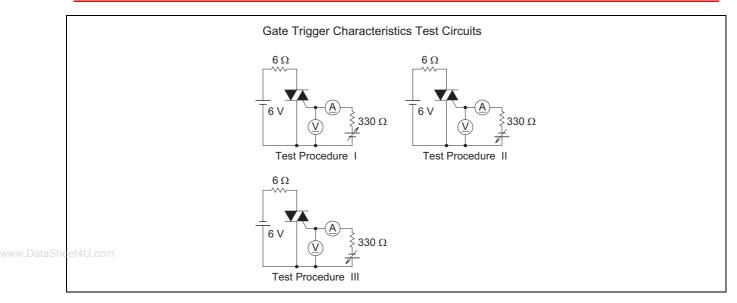
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured at the  $T_2$  terminal 1.5 mm away from the molded case.

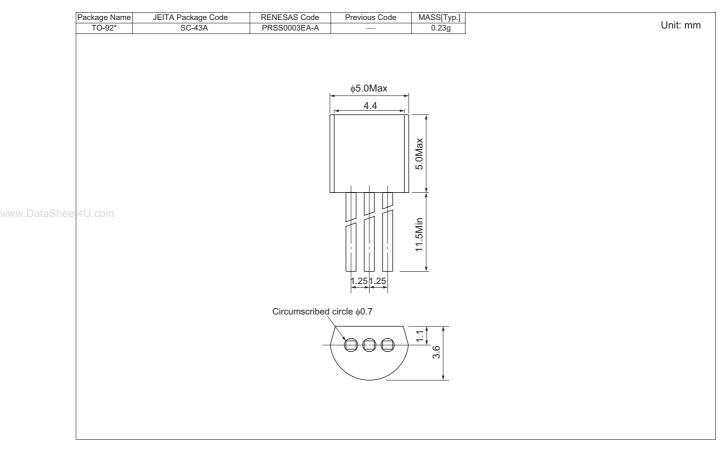
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage → Time
<ol> <li>Rate of decay of on-state commutating current (di/dt)c = - 0.5 A/ms</li> </ol>	Main Current → Time
3. Peak off-state voltage V <sub>D</sub> = 400 V	Main Voltage (dv/dt)c V <sub>D</sub>

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# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	500	Type name	BCR1AM-12A
Lead form	Vinyl sack	500	Type name – Lead forming code	BCR1AM-12A-A6
Form A8	Taping	2000	Type name – TB	BCR1AM-12A-TB

Note : Please confirm the specification about the shipping in detail.

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